N-Channel 250-V (D-S) 175 °C MOSFET

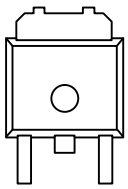
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
250	0.165 at V_{GS} = 10 V	17

FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature

RoHS COMPLIANT

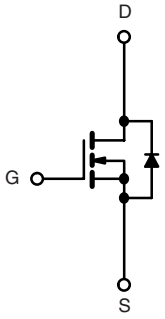
TO-252



G D S

Top View

Drain Connected to Tab



N-Channel MOSFET

Ordering Information: SUD17N25-165-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	250	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)[b]	T_C = 25 °C	I_D	17	A
	T_C = 125 °C		9.8	
Pulsed Drain Current		I_{DM}	20	
Continuous Source Current (Diode Conduction)		I_S	17	
Single Pulse Avalanche Current		I_{AS}	5	
Single Pulse Avalanche Energy	L = 0.1 mH	E_{AS}	1.25	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	136[b]	W
	T_A = 25 °C		3[a]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Junction-to-Case (Drain)		R_{thJC}	0.85	1.1	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

b. See SOA curve for voltage derating.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min**	**Typ[a]**	**Max**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	250			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.5		4.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 250 V, V_{GS} = 0 V			1	µA
		V_{DS} = 250 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 250 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 15 V, V_{GS} = 10 V	17			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 14 A		0.131	0.165	Ω
		V_{GS} = 10 V, I_D = 14 A, T_J = 125 °C			0.347	
		V_{GS} = 10 V, I_D = 14 A, T_J = 175 °C			0.462	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 17 A		36		S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		1950		pF
Output Capacitance	C_{oss}			160		
Reverse Transfer Capacitance	C_{rss}			70		
Total Gate Charge[c]	Q_g	V_{DS} = 125 V, V_{GS} = 10 V, I_D = 17 A		30	42	nC
Gate-Source Charge[c]	Q_{gs}			10		
Gate-Drain Charge[c]	Q_{gd}			10		
Gate Resistance	R_g			1.6		Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 125 V, R_L = 7.35 Ω I_D ≅ 17 A, V_{GEN} = 10 V, R_g = 2.5 Ω		15	25	ns
Rise Time[c]	t_r			130	195	
Turn-Off Delay Time[c]	$t_{d(off)}$			30	45	
Fall Time[c]	t_f			100	150	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)						
Pulsed Current	I_{SM}				20	A
Diode Forward Voltage[b]	V_{SD}	I_F = 17 A, V_{GS} = 0 V		0.9	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 17 A, di/dt = 100 A/µs		115	175	ns

Notes:

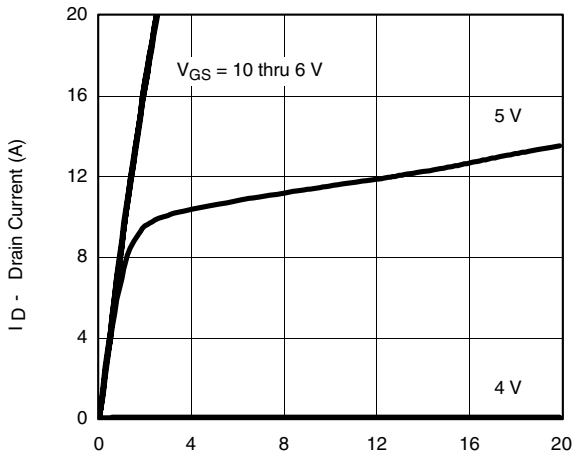
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

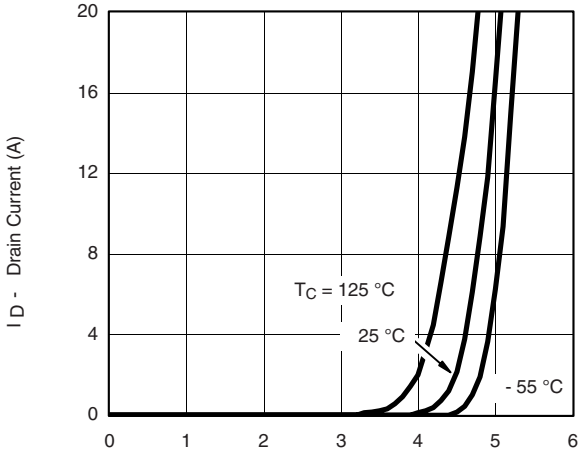
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

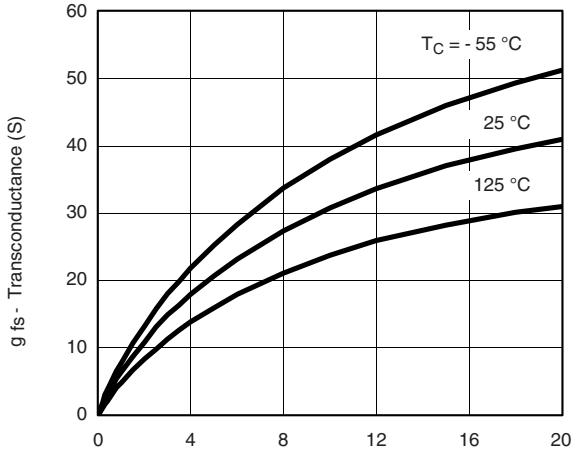
TYPICAL CHARACTERISTICS 25 °C unless noted



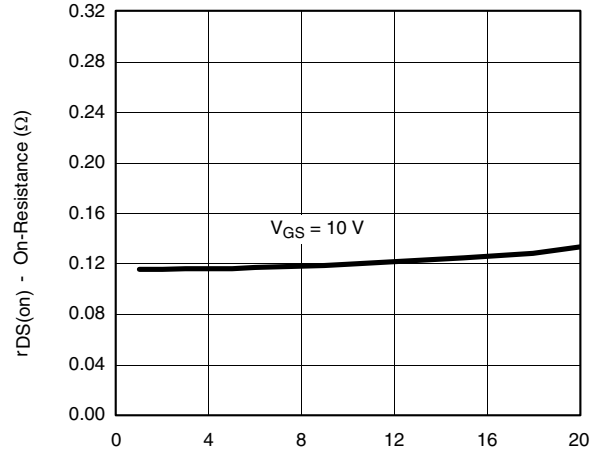
Output Characteristics



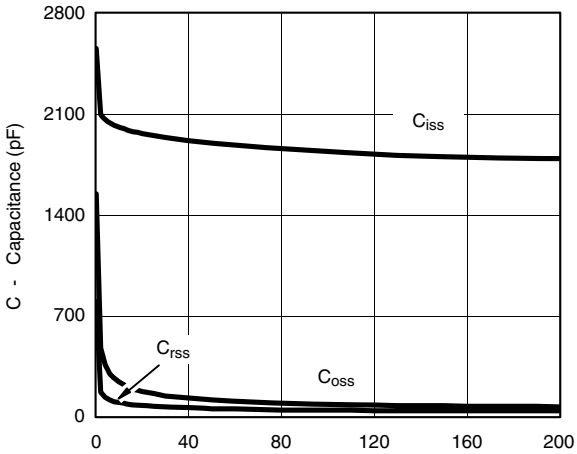
Transfer Characteristics



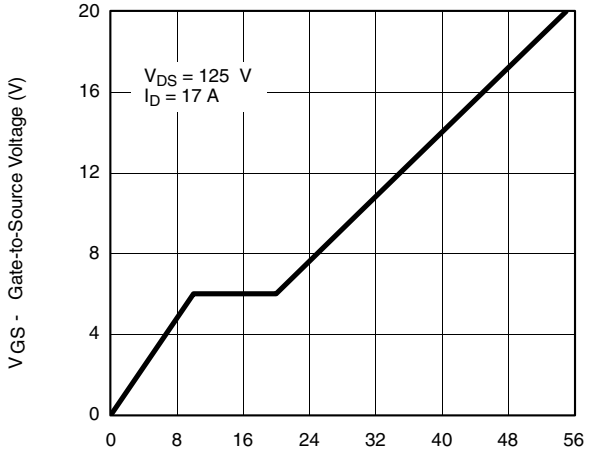
Transconductance



On-Resistance vs. Drain Current

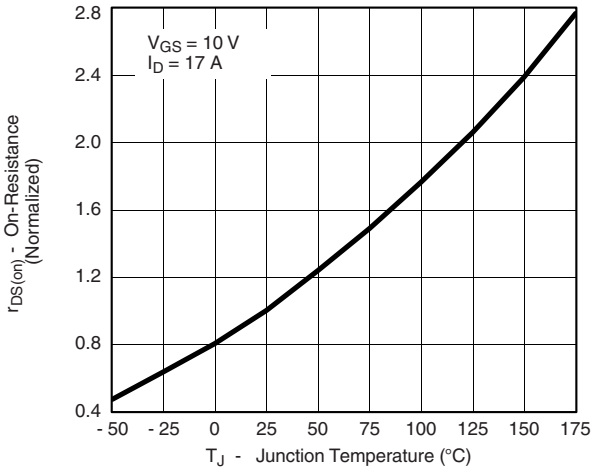


Capacitance

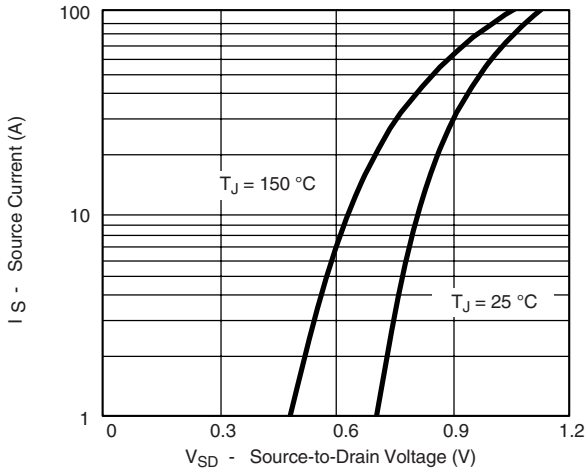


Gate Charge

TYPICAL CHARACTERISTICS 25 °C unless noted

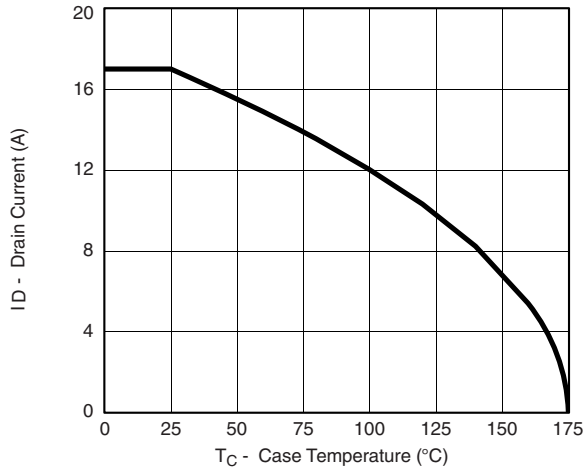


On-Resistance vs. Junction Temperature

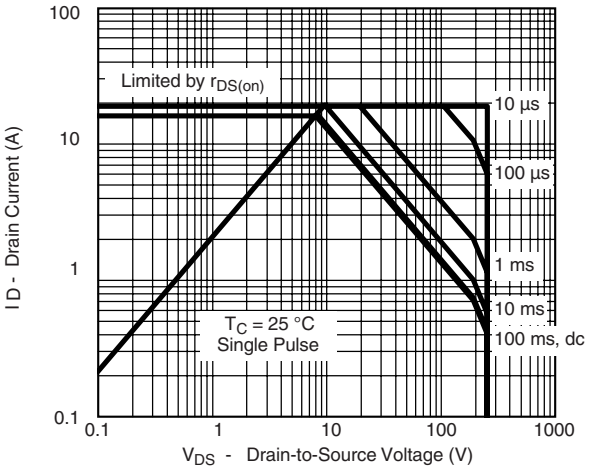


Source-Drain Diode Forward Voltage

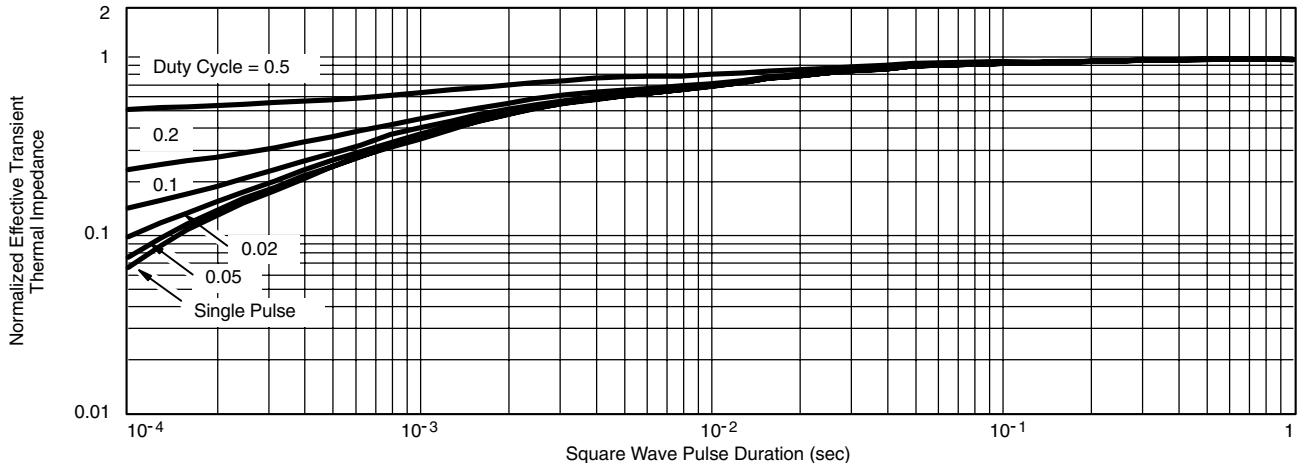
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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